



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Features

- $BV_{CEO} > -40V$
- $I_C = -200mA$ High Collector Current
- Epitaxial Planar Die Construction
- Ideal for Medium Power Amplification and Switching
- Ultra-Small Surface Mount Package
- Complementary NPN Type: NK-MMDT3904

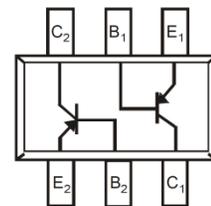
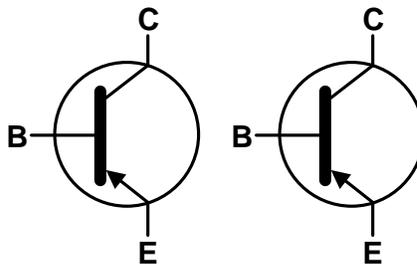
Mechanical Data

- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Finish; Solderable per MIL-STD-202, Method 208 ③
- Weight: 0.006 grams (Approximate)

SOT363



Top View



Device Schematic
Top View

Absolute Maximum Ratings

 (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-40	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-200	mA

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P_D	200	mW
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	625	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

ESD Ratings

 (Note 6)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes:
- For the device mounted on minimum recommended pad layout FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
 - Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristic and Derating Information

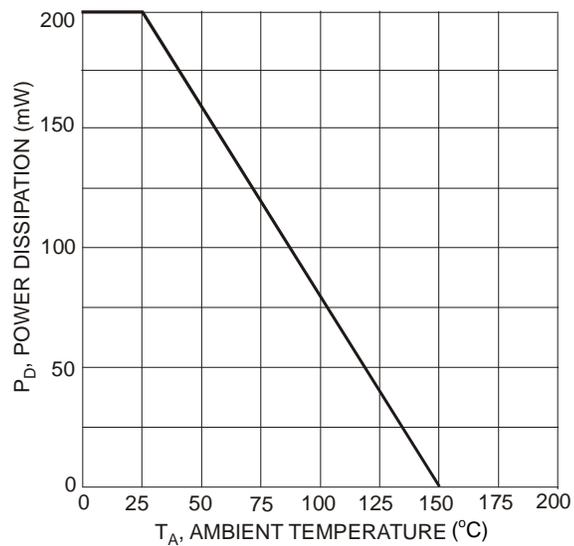


Fig. 1, Power Dissipation vs. Ambient Temperature (Total Device)

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition	
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV_{CBO}	-40	—	V	$I_C = -10\mu\text{A}, I_E = 0$	
Collector-Emitter Breakdown Voltage (Note 7)	BV_{CEO}	-40	—	V	$I_C = -1\text{mA}, I_B = 0$	
Emitter-Base Breakdown Voltage	BV_{EBO}	-5	—	V	$I_E = -10\mu\text{A}, I_C = 0$	
Collector Cut-Off Current	I_{CEX}	—	-50	nA	$V_{CE} = -30\text{V}, V_{EB(OFF)} = -3.0\text{V}$	
Base Cut-Off Current	I_{BL}	—	-50	nA	$V_{CE} = -30\text{V}, V_{EB(OFF)} = -3.0\text{V}$	
ON CHARACTERISTICS (Note 7)						
DC Current Gain	h_{FE}	60	—	—	$I_C = -100\mu\text{A}, V_{CE} = -1\text{V}$	
		80	—			$I_C = -1.0\text{mA}, V_{CE} = -1\text{V}$
		100	300			$I_C = -10\text{mA}, V_{CE} = -1\text{V}$
		60	—			$I_C = -50\text{mA}, V_{CE} = -1\text{V}$
		30	—			$I_C = -100\text{mA}, V_{CE} = -1\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	-0.25 -0.40	V	$I_C = -10\text{mA}, I_B = -1\text{mA}$ $I_C = -50\text{mA}, I_B = -5\text{mA}$	
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	-0.65 —	-0.85 -0.95	V	$I_C = -10\text{mA}, I_B = -1\text{mA}$ $I_C = -50\text{mA}, I_B = -5\text{mA}$	
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	C_{OBO}	—	4.5	pF	$V_{CB} = -5.0\text{V}, f = 1.0\text{MHz}, I_E = 0$	
Input Capacitance	C_{IBO}	—	10	pF	$V_{EB} = -0.5\text{V}, f = 1.0\text{MHz}, I_C = 0$	
Input Impedance	h_{ie}	2	12	k Ω	$V_{CE} = -10\text{V}, I_C = -1.0\text{mA},$ $f = 1.0\text{kHz}$	
Voltage Feedback Ratio	h_{re}	0.1	10	$\times 10^{-4}$		
Small Signal Current Gain	h_{fe}	100	400	—		
Output Admittance	h_{oe}	3	60	μS		
Current Gain-Bandwidth Product	f_T	250	—	MHz	$V_{CE} = -20\text{V}, I_C = -10\text{mA},$ $f = 100\text{MHz}$	
Noise Figure	N_F	—	4.0	dB	$V_{CE} = -5.0\text{V}, I_C = -100\mu\text{A},$ $R_S = 1.0\text{k}\Omega, f = 1.0\text{kHz}$	
SWITCHING CHARACTERISTICS						
Delay Time	t_D	—	35	ns	$V_{CC} = -3.0\text{V}, I_C = -10\text{mA},$ $I_{B1} = I_{B2} = -1.0\text{mA}$	
Rise Time	t_R	—	35	ns		
Storage Time	t_S	—	200	ns		
Fall Time	t_F	—	50	ns		

 Note: 7. Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$. Duty cycle $\leq 2\%$.

Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

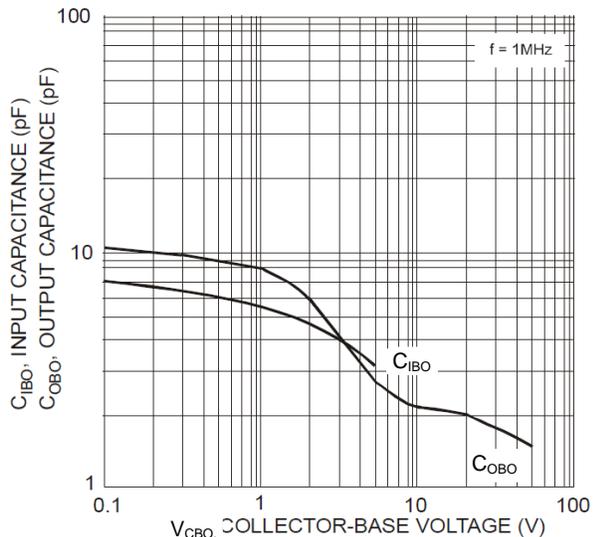


Fig. 2, Input and Output Capacitance vs. Collector-Base Voltage

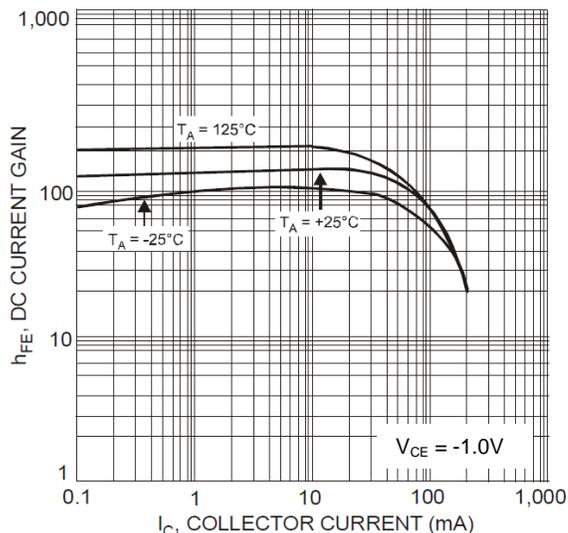


Fig. 3, Typical DC Current Gain vs. Collector Current

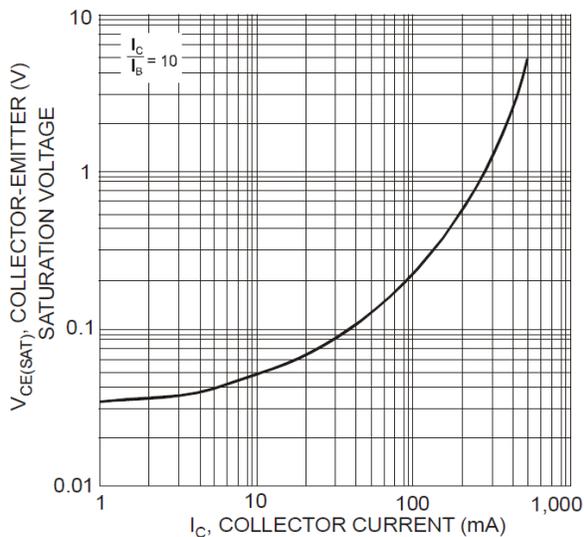


Fig. 4, Typical Collector-Emitter Saturation Voltage vs. Collector Current

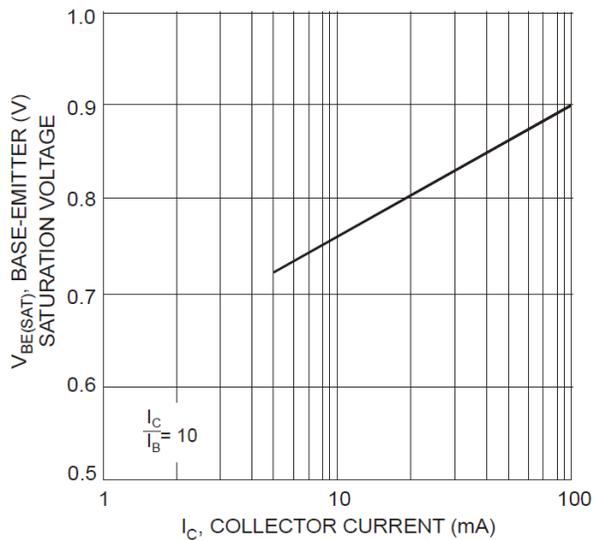
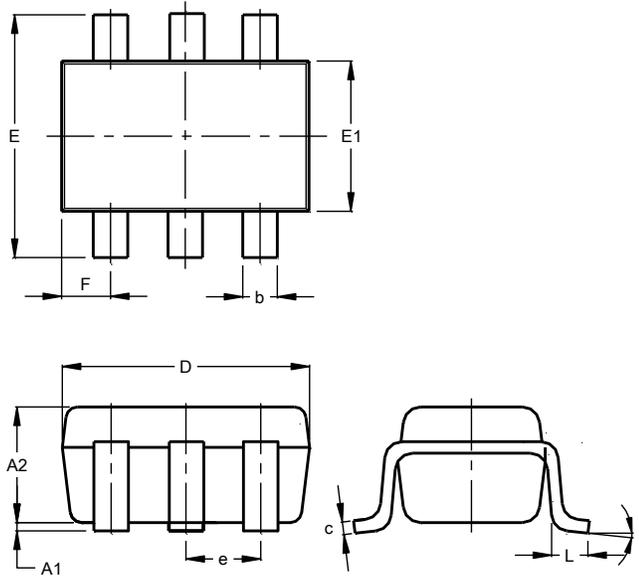


Fig. 5, Typical Base-Emitter Saturation Voltage vs. Collector Current

Package Outline Dimensions

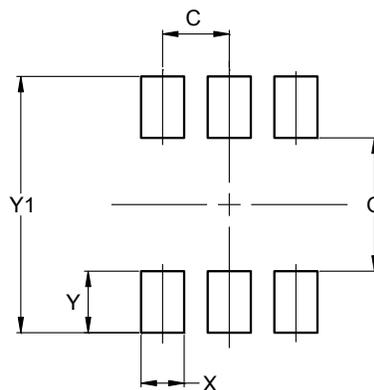
SOT363



SOT363			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.90	1.00	1.00
b	0.10	0.30	0.25
c	0.10	0.22	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
F	0.40	0.45	0.425
L	0.25	0.40	0.30
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

SOT363



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.420
Y	0.600
Y1	2.500